

Appl. No. : 10/074,633  
Filed : February 11, 2002

REMARKS

The specification has been amended as set forth above to rewrite the title and abstract, and to replace the previously recited attorney docket nos. with the serial numbers of the corresponding patent applications. Claim 19 has been amended to correct a minor typographical error. These amendments do not narrow the scope of the claims and do not introduce new matter.

Specific changes to the specification and the amended claims are shown on a separate set of pages attached hereto and entitled VERSION WITH MARKINGS TO SHOW CHANGES MADE, which follows the signature page of this Amendment. On this set of pages, the insertions are underlined while [deletions are bracketed and bolded].

Please charge any additional fees, including any fees for additional extension of time, or credit overpayment to Deposit Account No. 11-1410.

Respectfully submitted,

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Dated: 4/9/02

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE TITLE:**

DEPOSITION OVER MIXED SUBSTRATES [USING TRISILANE]

**IN THE ABSTRACT:**

[Trisilane is used in chemical] Chemical vapor deposition methods are used to deposit silicon-containing films over mixed substrates. Such methods are useful in semiconductor manufacturing to provide a variety of advantages, including uniform deposition over heterogeneous surfaces, high deposition rates, and higher manufacturing productivity. An example is in forming the base region of a heterojunction bipolar transistor, including simultaneous deposition over both single crystal semiconductor surfaces and amorphous insulating regions.

**IN THE SPECIFICATION:**

[0001] This application claims priority to U.S. Provisional Application No. 60/268,337, filed February 12, 2001; U.S. Provisional Application No. 60/279,256, filed March 27, 2001; U.S. Provisional Application No. 60/311,609, filed August 9, 2001; U.S. Provisional Application No. 60/323,649, filed September 19, 2001; U.S. Provisional Application No. 60/332,696, filed November 13, 2001; U.S. Provisional Application No. 60/333,724, filed November 28, 2001; and U.S. Provisional Application No. 60/340,454, filed December 7, 2001; all of which are hereby incorporated by reference in their entireties. This application is also related to, and incorporates by reference in their entireties, co-owned and co-pending U.S. Patent Application Serial Numbers: 10/074,563; 10/074,149; 10/074,722; 10/074,564; and 10/074,534, all of which were filed on February 11, 2002.

**IN THE CLAIMS:**

19. (Amended) A high-rate deposition method comprising:

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delivering trisilane to a mixed substrate surface under chemical vapor deposition conditions, at a delivery rate of at least about 0.001 milligrams per minute per square centimeter of the mixed substrate surface[,] ; and

depositing a silicon-containing material onto the mixed substrate surface at a rate of about 10 Å per minute or greater.